

Docket No.

## Declaration and Power of Attorney For Patent Application English Language Declaration

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name,

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled

METHOD AND APPARATUS FOR FORMING AN INTERLAYER INSULATING FILM AND SEMICONDUCTOR DEVICE

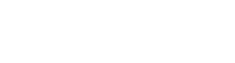
| the | specification of which |   |
|-----|------------------------|---|
| (ch | eck one)               |   |
| Ճ   | is attached hereto.    |   |
|     | was filed on           | as United States Application No. or PCT International |
|     | Application Number     |   |
|     | and was amended on     |   |
|     |                        | (if applicable)                                       |

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above.

I acknowledge the duty to disclose to the United States Patent and Trademark Office all information known to me to be material to patentability as defined in Title 37, Code of Federal Regulations, Section 1.56.

I hereby claim foreign priority benefits under Title 35, United States Code, Section 119(a)-(d) or Section 365(b) of any foreign application(s) for patent or inventor's certificate, or Section 365(a) of any PCT International application which designated at least one country other than the United States, listed below and have also identified below, by checking the box, any foreign application for patent or inventor's certificate or PCT International application having a filing date before that of the application on which priority is claimed.

| Prior Foreign Applicat | tion(s)   |                        | Priority Not Claimed |
|------------------------|-----------|------------------------|----------------------|
| 11-83180               | JAPAN     | 26/03/1999             |                      |
| (Number)               | (Country) | (Day/Month/Year Filed) | <b>—</b>             |
| (Number)               | (Country) | (Day/Month/Year Filed) | ·                    |
| (Number)               | (Country) | (Day/Month/Year Filed) |                      |



| · /A   |   | <del>.</del>   |
|--|---|--|
| (Application Serial No.)   | (Filing Date)   |  |
| (Application Serial No.)   | (Filing Date)   | -  |
| (Application Serial No.)   | (Filing Date)   |  |
| insofar as the subject matter of our United States or PCT International  | each of the claims of this ap<br>al application in the manner p   | plication is not disclosed in the pric<br>provided by the first paragraph of 3   |
| United States or PCT International U.S.C. Section 112, I acknowled Office all information known to r   | each of the claims of this ap<br>al application in the manner p<br>ge the duty to disclose to the<br>ne to be material to patentabable between the filing date of         | the United States, listed below and plication is not disclosed in the pricorovided by the first paragraph of 3 United States Patent and Trademar bility as defined in Title 37, C. F. R the prior application and the national |
| United States or PCT International U.S.C. Section 112, I acknowled Office all information known to resection 1.56 which became available.  | each of the claims of this ap<br>al application in the manner p<br>ge the duty to disclose to the<br>ne to be material to patentabable between the filing date of         | plication is not disclosed in the pric<br>provided by the first paragraph of 3<br>United States Patent and Trademar<br>pility as defined in Title 37, C. F. R  |
| United States or PCT International U.S.C. Section 112, I acknowled Office all information known to resection 1.56 which became available or PCT International filing date of the section 1.56 which became available or PCT International filing date of the section 1.56 which became available or PCT International filing date of the section 1.56 which became available or PCT International filing date of the section 1.56 which became available or PCT International filing date of the section 1.56 which is sec | each of the claims of this ap all application in the manner page the duty to disclose to the me to be material to patentable between the filing date of this application: | plication is not disclosed in the price provided by the first paragraph of 3 United States Patent and Trademar willity as defined in Title 37, C. F. R the prior application and the national (Status)                         |

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

nomination of the contract of

POWER OF ATTORNEY: As a named inventor, I hereby appoint the following attorney(s) and/or agent(s) to prosecute this application and transact all business in the Patent and Trademark Office connected therewith. (list name and registration number)

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| Full name of sole or first inventor           |    |      |     |      |
|---|----|------|-----|------|
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